

Control of applied electric field and temperature for different elemental composition in plasma-based nanofabrication

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Microscopic theory based on atomic ionization energy concept is developed to understand the evolution of the atomic and displacement polarizations with respect to the surface diffusion activation energy of adatoms in self-assembled quantum dots. We derive these polarizations classically and the atomic polarization is quantized to obtain the microscopic atomic polarizability. These polarizations as functions of the ionization energy can be used to study the evolution of surface diffusion activation energy of adatoms for different elemental composition in self-assembled quantum dots. In doing so, one can fine-tune the process parameters associated to the inductively coupled plasma chemical vapour deposition system, namely, the applied electric field and temperature for different elemental composition.

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I. INTRODUCTION

Self-organization and assembly of quantum dots (QDs) growth on surfaces exposed to low-temperature (T) plasmas play important roles on the growth of QDs with uniform size and distribution [1, 2]. The significant of such uniformity is to avoid the inhomogeneous broadening in quantized energy levels that may destroy the atomic-like properties from a single QD [3]. Interestingly, plasma-based nanofabrication technique possesses pronounced advantages to produce uniform QDs in terms of size distribution as well as the space distribution between the QDs [4]. This uniformity is extremely important for wide applications, for example in DNA-single electron transistor (nanoelectronics) [5], in photodynamic and radiation therapies (medicine) [6] and in nanophotonics (quantum information) [7]. Self-organization in large QD arrays, requires the consideration of surface diffusion in the presence of electric field [1]. Classically, one can take this effect into account by means of electric field gradient (with respect to QD's radius) and the electric dipole moment of adatoms. For example, Ostrikov et al. [1] have defined the energy taken by one jump across one lattice spacing as $W_e = |\partial \vec{E}_{\text{app}} / \partial r| \lambda_a p$, where \vec{E}_{app} , λ_a and p denote the applied electric field (external), lattice parameter and the electric dipole moment, respectively. In doing so, they concluded that larger electric field gradient (for smaller QDs) may increase the surface diffusion coefficient, which in turn gives rise to smaller surface diffusion activation energy. Eventually, this will lead to higher rates of adatoms leaving the smaller QDs, and these adatoms will be available to form new QDs [1]. The proportionality between diffusion coefficient and the rates of adatoms is an established fact based on the Nernst-Einstein relation-

ship [8]. As a consequence, one can surmise here that for a given (i) QDs (material), (ii) applied electric field, (iii) substrate material and (iv) temperature, one can control the uniformity of the QD arrays. In this work, another step forward is taken to study how the applied electric field and temperature need to be varied for different QDs on different substrates. In other words, how does one vary the process parameters for plasma based nanofabrication for various elemental compositions?. Answers to this question will provide us additional information to narrow down the magnitudes of the electric field and temperature required for different QDs on different substrates. In order to achieve this objective, one will need to microscopically derive the atomic polarizability and use it to derive the displacement polarizability of adatoms with respect to different elemental composition in QDs. In earlier work, a new method of handling the evolution of physical and electronic parameters microscopically have been developed that considers the effect of different elemental composition [9, 10, 11, 12, 13]. Here, this method will be applied to derive the above-stated polarizabilities in order to explain how we can change the applied electric field and temperature for different QDs. We will end our discussion by analyzing how does one goes about to fine-tune the applied electric field and temperature for different QDs using the plasma based nanofabrication tools.

II. THEORY OF THE POLARIZABILITY

A. Many-body Hamiltonian

We start from the dressed phonon frequency, which is given by [9, 10]

$$\omega(\xi, \mathbf{k}) = \frac{k\Omega_p}{K_s} \exp \left[\frac{1}{2} \lambda(\xi - E_F^0) \right]. \quad (1)$$

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Where, Ω_p is the plasma frequency and $K_s^2 = 3n_0e^2/2\epsilon_0E_F^0$. Here, n_0 and E_F^0 are the respective carrier density and the Fermi level or the highest occupied energy level for QDs, both at $T = 0$. k and K_s are the wavenumber and Thomas-Fermi wavenumber, respectively [9, 10]. Let us pause here and trace back the origin of this exponential term in Eq. (1) due to its importance in this work. This exponential term, which is a function of the ionization energy, ξ has been derived from the carrier density (n) equation as given below

$$n = \int_0^\infty f_e(E)N_e(E)dE, \quad (2)$$

where f_e and N_e are the ionization energy based electronic probability function and the density of states, respectively. Hence, it is easy to notice here that this exponential term comes from f_e , which is given by [10, 11]

$$f_e(E_0, \xi) = \frac{1}{e^{\lambda[(E_0+\xi)-E_F^0]} + 1}, \quad (3)$$

where $\lambda = (12\pi\epsilon_0/e^2)a_B$, a_B is the Bohr radius, e and ϵ_0 are the electronic charge and the permittivity of space, respectively [10]. For holes, one simply replaces the + sign in $E_0 + \xi$ (see Eq. (3)) with the sign, $-$. Next, the term $E_0 + \xi$ (total energy) in the probability function originated from the restrictive condition in the derivation of Eq. (3) (for example, study Refs. [9, 11]). And finally, the above-stated restrictive condition originated from our many-body Hamiltonian,

$$\hat{H}\varphi = (E_0 \pm \xi)\varphi. \quad (4)$$

The proofs of existence for Eq. (4) and its relation with many-electron atomic Hamiltonian are given in Ref. [9]. Having found the source of the exponential term, one can now work on the classical derivation of the atomic polarizability. After that, it is straight forward to transform the classical version to a quantum mechanical one, where the exponential term stays intact.

B. Atomic polarizability: Semiclassical

The original work on atomic polarizability entirely based on classical work was carried by Lorentz [14]. We will use the identical procedure, but with quantum mechanical properties incorporated into the interaction potential constant. Before going deeper into the polarizability, it is important to recall the implications of Eq. (1). As already shown in Ref. [9], the exponential term in Eq. (1) also implies that the harmonic potential energy (ϕ) for an atom is given by (see Fig. 1)

$$\phi(x) = \frac{1}{2}Z_i m x^2 \omega_0^2 \exp\left[\lambda(\xi - E_F^0)\right]. \quad (5)$$

Where, Z and m are the atomic number and i^{th} electronic mass, respectively, while ω_0 denotes the frequency of the vibration of the electronic shell (attached to the static nucleus via the spring as indicated in Fig. 1). The $Z_i e$ here represents the total charge of screened electrons with discrete energy levels, unlike the usual free-electrons as clearly depicted in Fig. 1. Therefore, the interaction potential constant, Q or also known as the spring constant can be obtained from Eq. (5),

$$Q = \frac{\partial^2 \phi}{\partial x^2} = Z_i m \omega_0^2 \exp\left[\lambda(\xi - E_F^0)\right]. \quad (6)$$

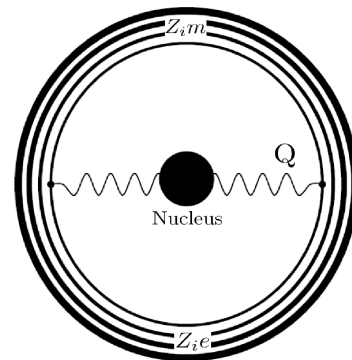


FIG. 1: Semiclassical model for the atomic polarizability with discrete energy levels, and with ξ as the energy level difference or the ionization energy. Recall that ξ changes with different atoms and so does the interaction potential constant or the so-called spring constant, Q . The discrete energy levels are for *non-free electrons* with total electronic charge $Z_i e$ and mass $Z_i m$.

Now, for mathematical convenience one can also write the frequency (ω) dependent, local electric field (\vec{E}) as [15]

$$\vec{E} = \vec{E}_0 e^{-i\omega(\xi)t}. \quad (7)$$

Where, $\omega(\xi) = \omega \exp[(\lambda/2)(\xi - E_F^0)]$. This simply means that the frequency dependent electric field can be varied accordingly for different atoms, so as to maintain the magnitude of the previous atomic polarizability.

For example, if one substitutionally dope C into Si sites to obtain $\text{Si}_{1-x}\text{C}_x$ QDs, then there will be a systematic change to the ionization energy (ξ) linearly as shown schematically in Fig. 2. As a consequence, the frequency of the electric field must increase exponentially with carbon doping (for example, see Eq. (7)), for a given temperature in order to maintain the magnitude of atomic polarizability between undoped Si and doped $\text{Si}_{1-x}\text{C}_x$. At a higher temperature, this increase in electric field frequency will be smaller. This linear relationship stated above is of course only valid if the valence states of carbon and silicon do not change in the course of doping, which

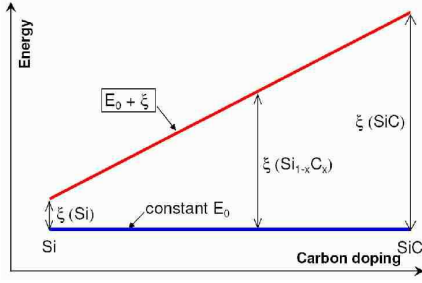


FIG. 2: The evolution of the ionization energy with C doping into Si sites (not to scale). Note here that E_0 is a constant and ξ captures the linear effect between energy and ξ (or doping).

is the case for $\text{Si}_{1-x}\text{C}_x$. If the valence states change for each doping, x , then this will lead to fluctuations in the linear relationship. The displacement, \mathbf{r} from its equilibrium, \mathbf{r}_0 due to the local electric field is given by [15]

$$\mathbf{r} = \mathbf{r}_0 e^{-i\omega(\xi)t}. \quad (8)$$

The equation of motion can be easily written as

$$F = Z_i m \ddot{\mathbf{r}} = -Q\mathbf{r} - Z_i e \vec{\mathbf{E}}_0 e^{-i\omega(\xi)t}. \quad (9)$$

Using Eq. (8), one can rewrite Eq. (9) to obtain

$$\mathbf{r}_0 = -\frac{e \vec{\mathbf{E}}_0}{m(\omega_0^2 - \omega^2)} \exp \left[\lambda(E_F^0 - \xi) \right]. \quad (10)$$

From the definition, the induced electric dipole moment, p is given by

$$\begin{aligned} p &= p_0 e^{-i\omega(\xi)t} = -Z_i e \mathbf{r} = \alpha(\omega, \xi) \vec{\mathbf{E}} \\ &= -\frac{Z_i e^2 \vec{\mathbf{E}}_0}{m(\omega_0^2 - \omega^2)} \exp \left[\lambda(E_F^0 - \xi) \right] e^{-i\omega(\xi)t} \\ \therefore \alpha &= \frac{Z_i e^2}{m(\omega_0^2 - \omega^2)} \exp \left[\lambda(E_F^0 - \xi) \right]. \end{aligned} \quad (11)$$

Where, $\alpha(\omega, \xi)$ is the frequency dependent atomic polarizability. The static polarizability is simply given by

$$\alpha(\xi) = \frac{Z_i e^2}{m\omega_0^2} \exp \left[\lambda(E_F^0 - \xi) \right]. \quad (12)$$

The exponential term derived in Eqs. (11) and (12) is in exact form compared to the atomic polarizability used in Ref. [11].

C. Atomic polarizability: Quantum mechanical

To derive the atomic polarizability quantum mechanically, one requires the understanding that real atoms are

not a continuous system but rather a multi discrete-level system. This means that atoms have more than one natural frequency, with each frequency has its own strength factor, f [16]. Hence the quantum mechanical version of Eq. (11) is simply given by (the spontaneous emission or classically known as the damping force is ignored for simplicity)

$$\alpha = \frac{Z_i e^2}{m} \exp \left[\lambda(E_F^0 - \xi) \right] \sum_j \frac{f_j}{(\omega_{0j}^2 - \omega^2)}. \quad (13)$$

This is indeed a straight forward transformation from Eq. (11) to Eq. (13). Our ignorance on the damping factor does not disturb the physics of elemental composition dependence that are being discussed here. In this transformation, the origin of the ionization energy in the exponential term ($e^{\lambda(E_F^0 - \xi)}$) is from the vibrational frequency, ω_0 , which is responsible for different atoms (different elemental composition) in a given compound. On the other hand, the strength factor (f_j) takes different modes of oscillations into account. The next issue that needs to be resolved is the displacement polarizability, which determines the rates of adatoms leaving the QDs during growth. We will address this in the following section.

D. Displacement polarizability: Semiclassical

Recall that the \mathbf{r} introduced earlier was due to electronic displacement and now the ionic (positively- and negatively-charged ions) displacement, \mathbf{u}^\pm will be studied. The dipole moment of the primitive cell is given by [15]

$$P = e(\mathbf{u}^+ - \mathbf{u}^-) = e\mathbf{d}. \quad (14)$$

Note here that we are *not* assuming that the ions are undeformable, as was done in Ref. [15], because the interaction potential constant (G), which is introduced below is identical with the one given in Eq. (6). This newly defined potential constant takes the ionic deformation due to the screened core electrons into account via the exponential term. Using Eq. (14), the equations of motion can be written as

$$F^+ = M^+ \ddot{\mathbf{u}}^+ = -G\mathbf{d} + e\vec{\mathbf{E}}. \quad (15)$$

$$F^- = M^- \ddot{\mathbf{u}}^- = -G(-\mathbf{d}) - e\vec{\mathbf{E}}. \quad (16)$$

Where, $-\mathbf{d}$ that appears in Eq. (16) arises as a result of the opposite directions of F^+ and F^- . Now, to obtain the total force, F , that causes the displacement, \mathbf{d} one can write $F = F^+ - F^-$ to obtain (from Eqs. (15) and (16))

$$\ddot{\mathbf{d}} = -G\mathbf{d} \left[\frac{1}{M^+} + \frac{1}{M^-} \right] + e\vec{\mathbf{E}} \left[\frac{1}{M^+} + \frac{1}{M^-} \right]. \quad (17)$$

After taking $1/M = 1/M^+ + 1/M^-$, using Eq. (7) for the electric field, and using equations similar to Eqs. (5) and (6) for G , one can arrive at

$$\begin{aligned} \mathbf{d} &= \mathbf{d}_0 e^{-i\omega(\xi)t} \\ \mathbf{d}_0 &= \frac{e\vec{\mathbf{E}}_0}{M(\omega_{\text{ph}}^2 - \omega^2)} \exp \left[\lambda(E_F^0 - \xi) \right]. \end{aligned} \quad (18)$$

Using the definition of the atomic polarizability given in Eq. (11), one can derive the displacement polarizability as

$$\alpha_d = \frac{e}{M} \left[\frac{\exp[\lambda(E_F^0 - \xi)]}{(\omega_{\text{ph}}^2 - \omega^2)} \right]. \quad (19)$$

Carefully note here that Eq. (19) is the displacement polarizability for deformable ions. If, $\lim_{\xi \rightarrow \infty} \exp[\lambda(E_F^0 - \xi)] = 0$, then the ions are infinitely rigid, $\alpha_d \rightarrow 0$. On the other hand, $\lim_{\xi \rightarrow E_F^0} \exp[\lambda(E_F^0 - \xi)] = 1$ implies undeformable ions, because the ions radii are constant due to constant E_F^0 . For example, study the theory of electron-phonon interaction given in Ref. [9]. In other words, the ions deformability in the presence of the screened electrons has been taken into account via the interaction potential constant, G , which is a function of the ionization energy (ξ). Therefore, one does not need to employ the naive way of adding Eq. (19) and Eq. (11) for both positive and negative ions to obtain the total polarizability, as used in Ref. [15]. Furthermore, one *can* include the polarizability of the core electrons by simply calculating ξ accurately for those core electrons of each ion in a given compound. Such calculations have been carried out by Woods et al. [17] for alkali halide crystals using a different approach known as the Shell Model theory with appropriately introduced different types of short-ranged interaction potential constants, Φ_{xy} . In our theory however, G takes care of that via the exponential term for different elemental composition.

III. EFFECT OF IONIZATION ENERGY ON CONTROL PARAMETERS

Having derived all the relevant equations, the readers can now try to understand the microscopic mechanisms involved in adatoms leaving the QDs in the presence of applied electric field and temperature for different QDs and elemental composition. Using the macroscopic formulation of Ostrikov-Levchenko-Xu [1, 18, 19], we can write the dimensionless energy as [1]

$$\epsilon_e = \frac{\lambda_a}{k_B T} \frac{\partial \vec{\mathbf{E}}_{\text{app}}}{\partial r} [p + \alpha \vec{\mathbf{E}}_{\text{app}}], \quad (20)$$

which can be associated to the surface diffusion coefficient [1], or also known as the surface diffusivity,

$$D_S = \lambda_a^2 \nu_0 \exp \left[\frac{\epsilon_e - \epsilon_d}{k_B T} \right], \quad (21)$$

where $\nu_0 = 2k_B T/h$, denotes the lattice oscillation frequency, h is the Planck's constant, r represents the QD's radius and ϵ_d is the surface diffusion activation energy. Equations (20) and (21) implies that for large applied electric field gradient, $\partial \vec{\mathbf{E}}_{\text{app}}/\partial r$ one also has large ϵ_e and D_S . Any increment in non-dimensional energy, ϵ_e simply implies increased in surface diffusivity, D_S because large ϵ_e reduces the effect of ϵ_d as shown in Eq. (21). Simply put, any increment in ϵ_e will lead to the conclusion of decreased surface diffusion activation energy ($\epsilon_e - \epsilon_d$) and higher rates of adatoms leaving the smaller QDs that will be available to form new QDs [1]. Now, it is possible to incorporate the previous microscopic results given in Eq. (19) into Eq. (20) to arrive at

$$\begin{aligned} \epsilon_e &= \frac{\lambda_a}{k_B T} \frac{\partial \vec{\mathbf{E}}_{\text{app}}}{\partial r} \alpha_d [\vec{\mathbf{E}} + \vec{\mathbf{E}}_{\text{app}}], \\ &= \frac{\lambda_a e}{k_B T M} \left[\frac{e^{\lambda(E_F^0 - \xi)}}{\omega_{\text{ph}}^2} \right] \frac{\partial \vec{\mathbf{E}}_{\text{app}}}{\partial r} [\vec{\mathbf{E}} + \vec{\mathbf{E}}_{\text{app}}]. \end{aligned} \quad (22)$$

We can describe three physical mechanisms based on Eq. (22). For a given QD material, any changes to the applied electric field and temperature will also change the adatoms diffusivity accordingly, as simulated in the Refs. [1, 4]. The other two mechanisms are related to the systematic changes in elemental composition either due to (i) size or (ii) for an entirely new QD material. The point (i) arises from the known simulation results where the elemental composition of $\text{Si}_{1-x}\text{C}_x$ changes during QDs growth [20]. Whereas, point (ii) is obvious because of different material for QDs is used. For the latter two points, one can fix the temperature and applied electric field, and any systematic changes in elemental composition also changes the non-dimensional energy due to changes in the ionization energy (see Eq. (22)). As a result of this, the adatoms diffusivity also fluctuates accordingly. Simply put, if one considers the $\text{Si}_{1-x}\text{C}_x$ QDs, then the average ionization energy value for Si and C can be calculated as, $\xi_{\text{Si}^{4+}} = 2488 \text{ kJ mol}^{-1}$ and $\xi_{\text{C}^{4+}} = 3571 \text{ kJ mol}^{-1}$, where the ionization energy values prior to averaging were obtained from Ref. [21]. Apparently, $\xi_{\text{Si}^{4+}} < \xi_{\text{C}^{4+}}$, therefore from Eqs. (21) and (22) one has a higher diffusivity for Si compared to C, $D_S^{\text{Si}^{4+}} > D_S^{\text{C}^{4+}}$. This is a telling sign that at a higher temperature and/or at a higher applied electric field, one will always have higher rates of evaporation and diffusion for Si ions compared to C. In such cases, one needs to control the influx of the Si ions more rigorously with growth time as compared to carbon since the latter ion (carbon) has low diffusivity and rates of evaporation from the surface of a given substrate.

IV. CONCLUSIONS

We have derived both the semiclassical and quantum mechanical version of atomic polarizability that treats all the electrons as strongly correlated with discrete energy levels. Subsequently, the derivation for the displacement polarizability as a function of ionization energy enabled us to get rid of the undeformable-ion formalism. Consequently, one do not need to employ any naive approximation to obtain the total polarizability in order to evaluate the effect of applied electric field and temperature on different ions in quantum dots. We further find that by knowing how the ionization energy changes for different element composition, one can actually fine-tune the temperature and the applied electric field to grow the required QDs with a particular composition. Apart from that, we may also control the influx of a certain

ion, namely, the one with lower ionization energy that has a strong tendency to diffuse on the surface and/or evaporate from the surface. Therefore, it is shown here that one can control the essential parameters in nanofabrication tools to engineer the growth of quantum dots efficiently.

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